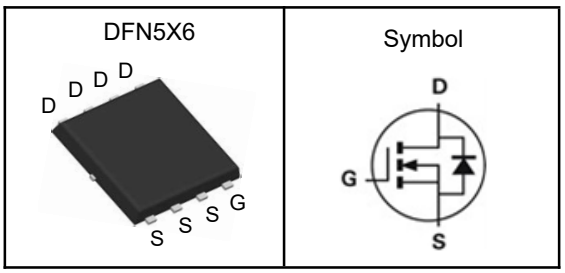
N-Channel Enhancement Mode MOSFET

Features

- Fast switching speed
- Reliable and Rugged
- ROHS Compliant
- 100% UIS and Rg Tested

Pin Description



Applications

- Power Management in Desktop Computer
- DC/DC Converters

V_{DSS}	80	V
$R_{DS(ON)-Typ}$	2.9	mΩ
I_D	17	A

Absolute Maximum Ratings(T_C=25℃, Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
V_{DSS}	Drain-Source Voltage		80	V
V_{GSS}	Gate-Source Voltage		±20	V
T_J	Maximum Junction Temperature		-55 to 150	℃
T_{STG}	Storage Temperature Range		-55 to 150	℃
EAS	Single Pulse Avalanche Energy③		937	mJ
I_{DM} ①	Pulse Drain Current Tested		400	A
I_D	Continuous Drain Current	T_C=25°C	17	A
P_D	Maximum Power Dissipation	T_C=25°C	125	W

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	50	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case①	1.0	℃/W

Note ①：Max. current is limited by bonding wire.

Note ②：UIS tested and pulse width are limited by maximum junction temperature 150℃.

Note ③：Surface Mounted on 1in^2 FR-4 board with 1oz.

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Electrical Characteristics (T_J=25℃, Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	80	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=80V, V_{GS}=0V	---	---	1	uA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} , I_D=250uA	2.0	3.0	4.0	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V	---	---	±100	nA
$R_{DS(ON)}$	Drain-Source On-state Resistance	V_{GS}=10V, I_D=20A	---	2.9	3.8	mΩ
		V_{GS}=6V, I_D=20A	---	4.5	6	mΩ
Dynamic Characteristics⑤						
C_{iss}	Input Capacitance	V_{DS}=40V, V_{GS}=0V, Freq.=1MHz	---	5290	---	pF
C_{oss}	Output Capacitance		---	870	---	
C_{rss}	Reverse Transfer Capacitance		---	10	---	
$T_{d(on)}$	Turn-on Delay Time	V_{DS}=40V,V_{GS}=10V , I_D=55A,R_G=2.2Ω	---	22	---	nS
T_r	Turn-on Rise Time		---	160	---	
$T_{d(off)}$	Turn-off Delay Time		---	34	---	
T_f	Turn-off Fall Time		---	10	---	
Q_g	Total Gate Charge	V_{DS}=40V,V_{GS}=10V , I_D=55A	---	68	---	nC
Q_{gs}	Gate-Source Charge		---	20	---	
Q_{gd}	Gate-Drain Charge		---	13	---	
Source-Drain Characteristics						
V_{SD}	Diode Forward Voltage	I_S=55A, V_{GS}=0V	---	---	1.2	V
t_{rr}	Reverse Recovery Time	I_F=55A,V_{GS}=0V, dI_F/dt=420A/us	---	73	---	nS
Q_{rr}	Reverse Recovery Charge		---	36	---	nC

Note ④： Pulse test (pulse width≤300us, duty cycle≤2%).

Note ⑤ : Guaranteed by design, not subject to production testing.

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Typical Characteristics

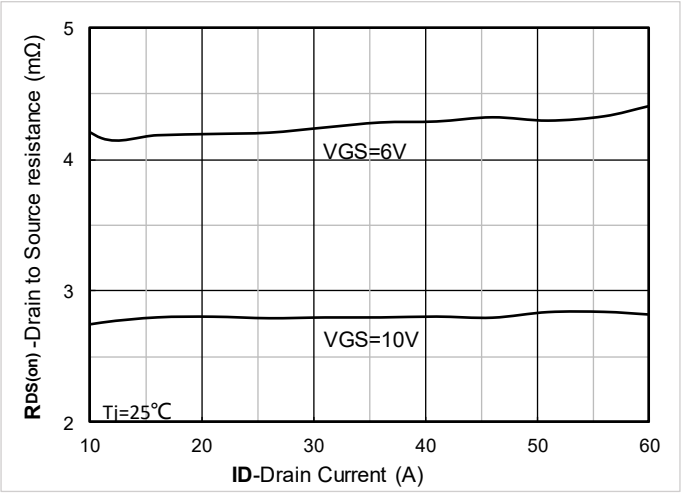

Figure 1. $R_{DS(on)}$ VS Drain Current

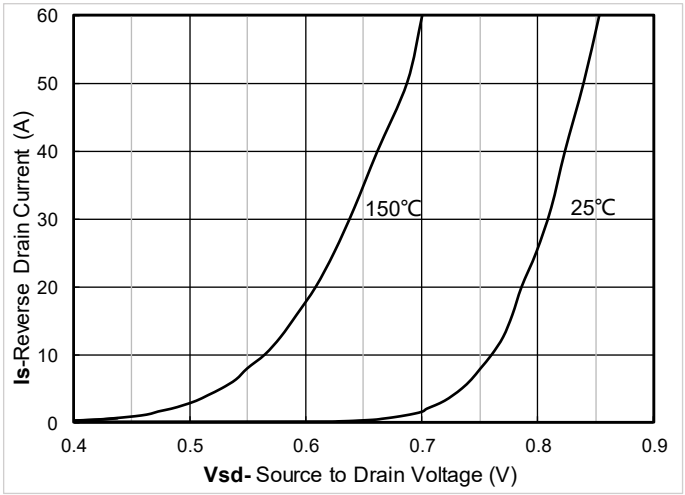

Figure 2. Forward characteristics of reverse diode

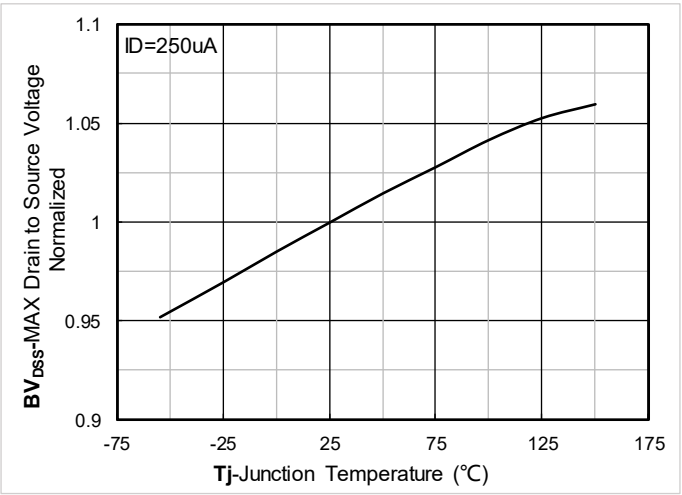

Figure 3. Normalized breakdown voltage

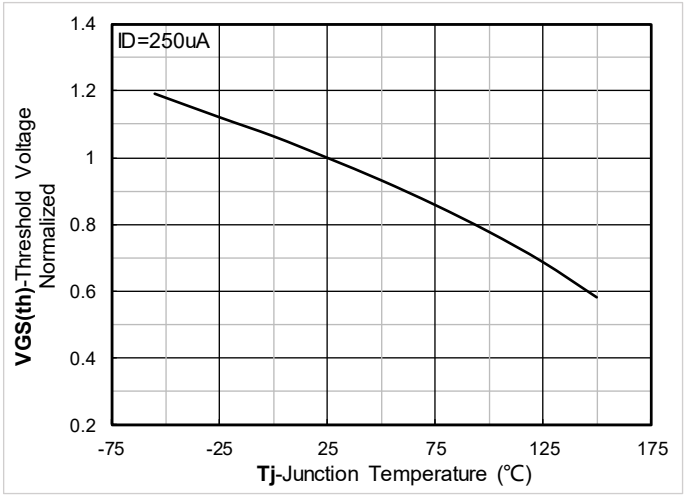

Figure 4. Normalized Threshold voltage

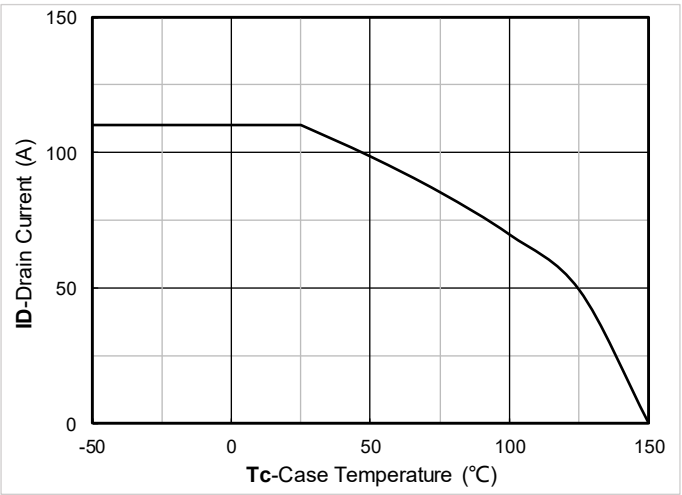

Figure 5. Current dissipation

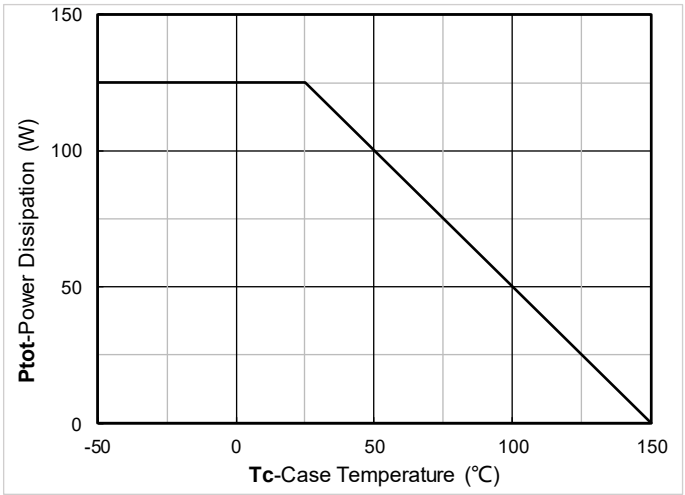

Figure 6. Power dissipation

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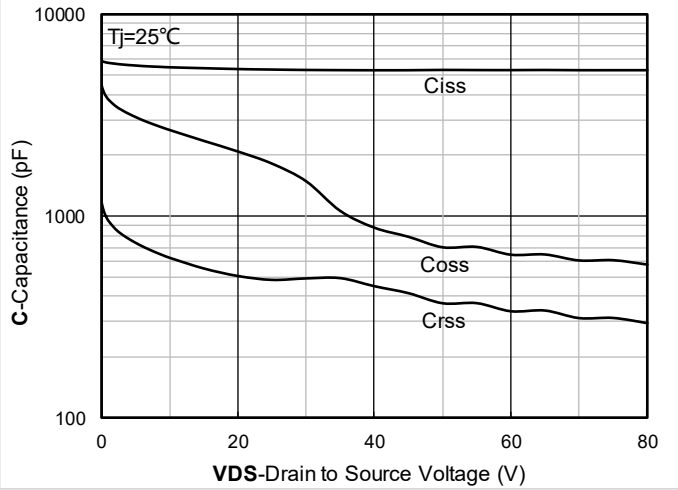

Figure 7. Capacitance Characteristics

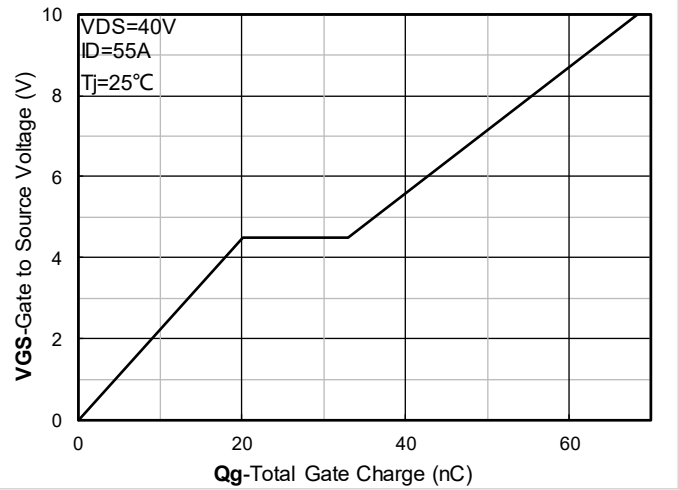

Figure 8. Gate Charge

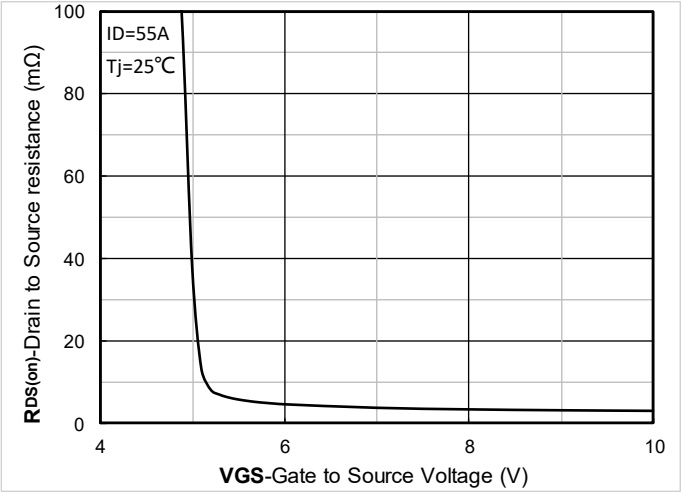

Figure 9. On-Resistance vs Gate to Source Voltage

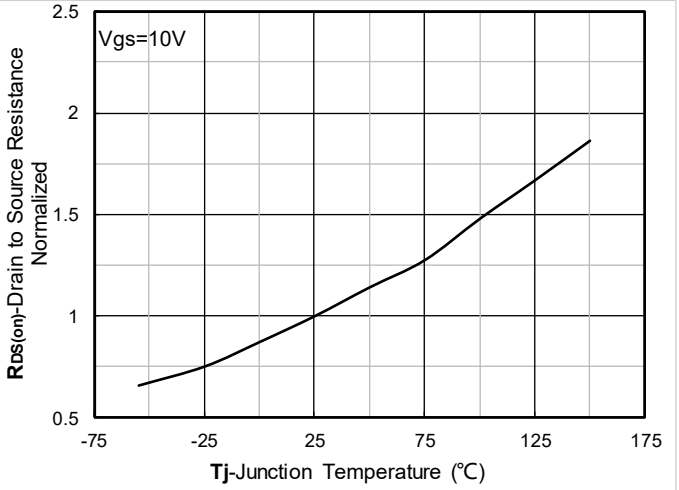

Figure 10. Normalized On-Resistance

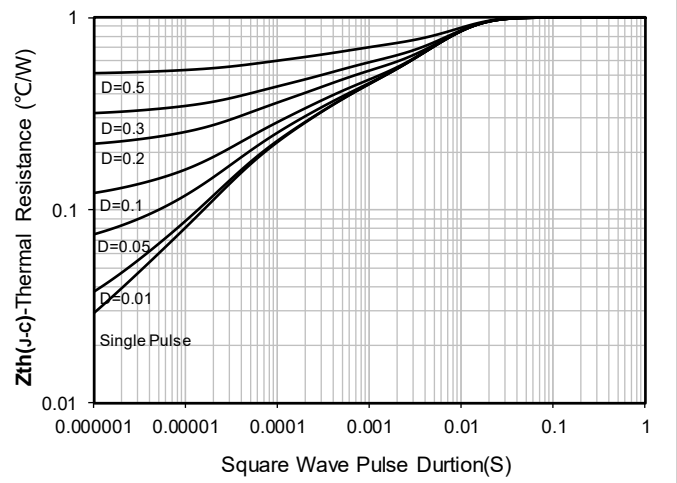

Figure 11. Maximum Transient Thermal Impedance

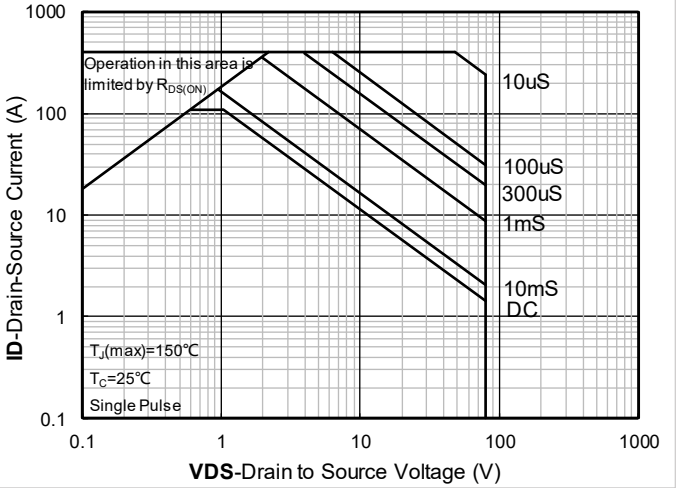

Figure 12. Safe Operation Area

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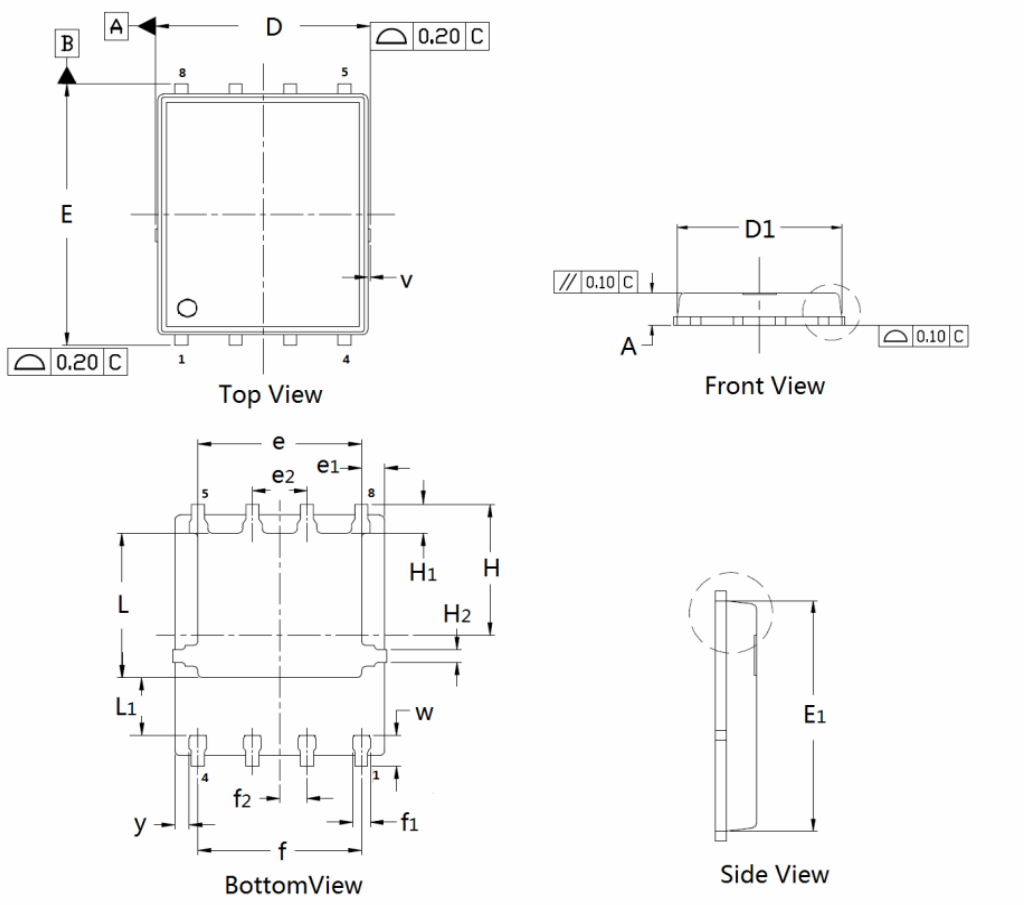
DFN5×6 Package Outline Data



DIMENSIONS (unit : mm)

Symbol		Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.02	1.10	**D**	4.90	4.98	5.10
D_1	4.80	4.89	5.10	**E**	5.90	6.11	6.25
E_1	5.65	5.74	5.95	**e**	3.72	3.80	3.92
e_1	--	0.5	--	**e_2**	--	1.	--
f	--	3.8	--	**f_1**	0.31	0.37	0.51
f_2	--	0.6	--	**H**	--	3.	--
H_1	0.59	0.63	0.79	**H_2**	0.26	0.28	0.32
L	3.35	3.45	3.65	**L_1**	--	1.	--
v	--	0.1	--	**w**	0.64	0.68	0.84
y	--	0.3	--		--		--